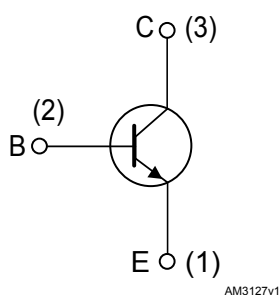
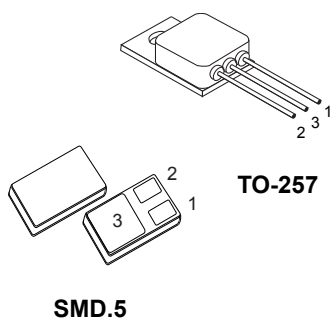


## Rad-Hard 80 V, 5 A NPN transistor



Base and Emitter are inverted for 2N5154RSRHRx and 2N5154SRHRx series. For TO-257, the case is not connected to any pin. For SMD.5, the lid is not connected to any pin.

### Product status link

[2N5154HR](#)

## Features

$V_{CEO}$	$I_C(\text{max.})$	$h_{FE}$ at 5 V, 2.5 A	Operating temperature range
80 V	5 A	> 70	-65 °C to +200 °C

- Hermetic package
- ESCC qualified
- Up to 100 krad(Si) low dose rate

## Description

The 2N5154HR is a silicon planar epitaxial NPN transistor in TO-257 and SMD.5 packages. It is specifically designed for Rad-Hard applications and ESCC qualified according to the 5203/010 specification.

In case of discrepancies between this datasheet and the relevant agency specification, the latter takes precedence.

## Product summary

Product summary				
Device	Qualification system	Agency specification	Package	Remarks
2N5154ESYHRx	ESCC	5203/010	TO-257	-
2N5154RESYHRx	ESCC	5203/010	TO-257	100 krad ESCC LDR
2N5154RSRHRx	ESCC	5203/010	SMD.5	100 krad LDR, emitter on pin 1
2N5154SHRxx	ESCC	5203/010	SMD.5	Emitter on pin 1
2N5154RSRHRx	ESCC	5203/010	SMD.5	100 krad LDR, emitter on pin 1
2N5154SRHRx	ESCC	5203/010	SMD.5	Emitter on pin 2

Note: See [Table 7](#) for ordering information.

## 1 Electrical ratings

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	100	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	80	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	6	V
$I_C$	Collector current	5	A
$P_{TOT}$	Total dissipation at $T_{amb} \leq 25\text{ °C}$ for TO-257 and SMD.5	3.3	W
	Total dissipation at $T_{case} \leq 25\text{ °C}$ for TO-257 and SMD.5	35	W
$T_{OP}$	Operating temperature range	-65 to 200	°C
$T_J$	Max. operating junction temperature	200	°C

**Table 2. Thermal data**

Symbol	Parameter	TO-257 and SMD.5 value	Unit
$R_{thj-case}$	Thermal resistance junction-case	5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	53	°C/W

## 2 Electrical characteristics

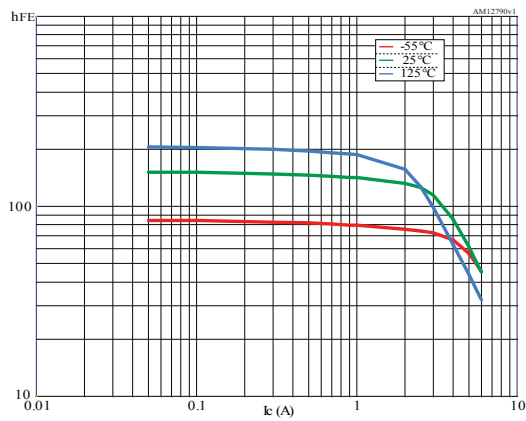
**Table 3. Electrical characteristics ( $T_{amb} = 25\text{ °C}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Max.	Unit
$I_{CES}$	Collector cut-off current	$V_{CB} = 60\text{ V}, I_E = 0\text{ A}$		1	$\mu\text{A}$
		$V_{CB} = 60\text{ V}, I_E = 0\text{ A},$ $T_{amb} = 150\text{ °C}$		10	
$I_{CEO}$	Collector cut-off current	$V_{CE} = 40\text{ V}, I_B = 0\text{ A}$		50	$\mu\text{A}$
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 5\text{ V}, I_C = 0\text{ A}$		1	$\mu\text{A}$
		$V_{EB} = 6\text{ V}, I_C = 0\text{ A}$		1	$\text{mA}$
$V_{(BR)CEO}^{(1)}$	Collector-emitter breakdown voltage	$I_C = 100\text{ mA}, I_B = 0\text{ A}$	80		$\text{V}$
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = 2.5\text{ A}, I_B = 0.25\text{ A}$		1.45	$\text{V}$
		$I_C = 5\text{ A}, I_B = 0.5\text{ A}$		1.5	
$V_{BE(sat)}^{(1)}$	Base-emitter saturation voltage	$I_C = 2.5\text{ A}, I_B = 0.25\text{ A}$		1.45	$\text{V}$
		$I_C = 5\text{ A}, I_B = 0.5\text{ A}$		2.2	
$h_{FE}^{(1)}$	DC current gain	$I_C = 50\text{ mA}, V_{CE} = 5\text{ V}$	50		
		$I_C = 2.5\text{ A}, V_{CE} = 5\text{ V}$	70	200	
		$I_C = 5\text{ A}, V_{CE} = 5\text{ V}$	40		
		$I_C = 2.5\text{ A}, V_{CE} = 5\text{ V}, T_{amb} = -55\text{ °C}$	35		
$h_{fe}$	AC forward current transfer ratio	$I_C = 500\text{ mA}, f = 20\text{ MHz}, V_{CE} = 5\text{ V}$	3.5		
$C_{obo}$	Output capacitance	$I_E = 0\text{ A}, f = 1\text{ MHz}, V_{CB} = 10\text{ V}$		250	$\text{pF}$
$t_{on}$	Turn-on time	$V_{CC} = 30\text{ V}, V_{BB} = -4\text{ V},$		0.5	$\mu\text{s}$
$t_{off}$	Turn-off time	$V_{in} \approx 51\text{ V}, I_C = 5\text{ A},$ $I_{B1} = -I_{B2} = 0.5\text{ A}$		1.3	$\mu\text{s}$

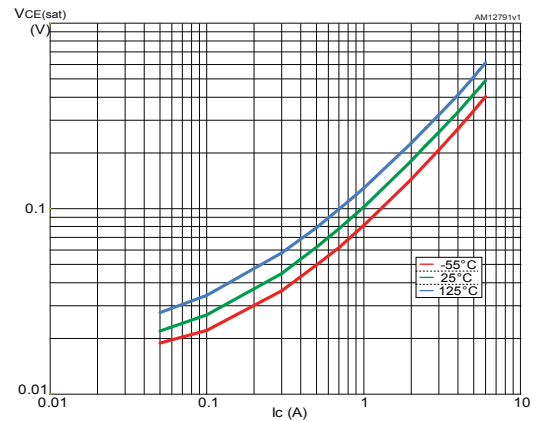
1. Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 2\%$

### 3 Electrical characteristics (curves)

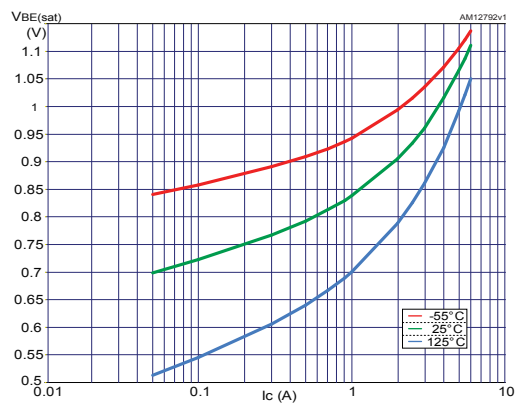
**Figure 1.  $h_{FE}$  at  $V_{CE} = 5\text{ V}$**



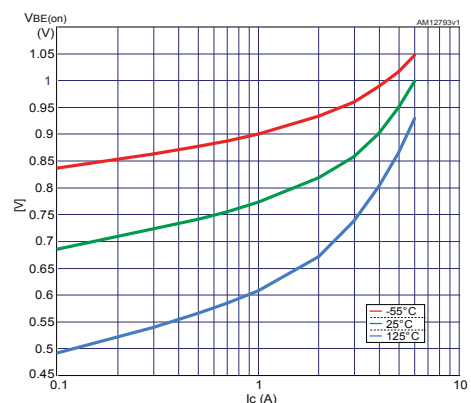
**Figure 2.  $V_{CE(sat)}$  at  $h_{FE} = 10$**



**Figure 3.  $V_{BE(sat)}$  at  $h_{FE} = 10$**

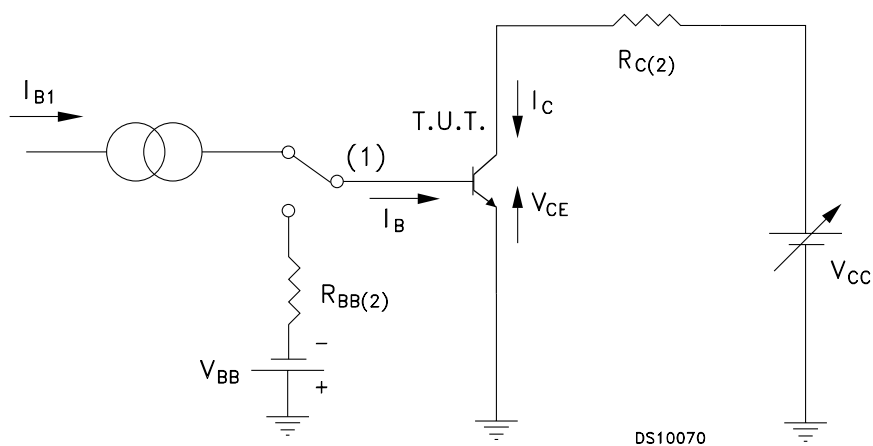


**Figure 4.  $V_{BE(on)}$  at  $V_{CE} = 5\text{ V}$**



### 3.1 Test circuits

**Figure 5. ESCC resistive load switching test circuit**



Note: (1) Fast electronic switch

Note: (2) Non-inductive resistor

## 4 Radiation hardness assurance

This products is guaranteed in radiation as per ESCC 22900 and in compliance with ESCC 5203/010 specification.

Each lot is tested in radiation according to the following procedure:

- Radiation condition of 0.1 rad (Si)/s
- Test of 11 samples by wafer, 5 biased at 80% of  $V_{(BR)CEO}$ , 5 unbiased and for reference
- Acceptance criteria of each wafer at 100 krad if all 10 samples comply with the post radiation electrical characteristics as per Table 4.

**Table 4. ESCC 5203/010 post radiation electrical characteristics ( $T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Max.	Unit
$I_{CES}$	Collector cut-off current	$V_{CB} = 60\text{ V}$ , $I_E = 0\text{ A}$		1	$\mu\text{A}$
$I_{CEO}$	Collector cut-off current	$V_{CE} = 40\text{ V}$ , $I_B = 0\text{ A}$		50	$\mu\text{A}$
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 5\text{ V}$ , $I_C = 0\text{ A}$		1	$\mu\text{A}$
		$V_{EB} = 6\text{ V}$ , $I_C = 0\text{ A}$		1	$\text{mA}$
$V_{(BR)CEO}^{(1)}$	Collector-emitter breakdown voltage	$I_C = 100\text{ mA}$ , $I_B = 0\text{ A}$	80		V
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = 2.5\text{ A}$ , $I_B = 0.25\text{ A}$		1.45	V
		$I_C = 5\text{ A}$ , $I_B = 0.5\text{ A}$		1.5	
$V_{BE(sat)}^{(1)}$	Base-emitter saturation voltage	$I_C = 2.5\text{ A}$ , $I_B = 0.25\text{ A}$		1.45	V
		$I_C = 5\text{ A}$ , $I_B = 0.5\text{ A}$		2.2	
$[h_{FE}]^{(1)}$	Post irradiation gain calculation <sup>(2)</sup>	$I_C = 50\text{ mA}$ , $V_{CE} = 5\text{ V}$	[25]		
		$I_C = 2.5\text{ A}$ , $V_{CE} = 5\text{ V}$	[35]	200	
		$I_C = 5\text{ A}$ , $V_{CE} = 5\text{ V}$	[20]		

1. Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 2\%$

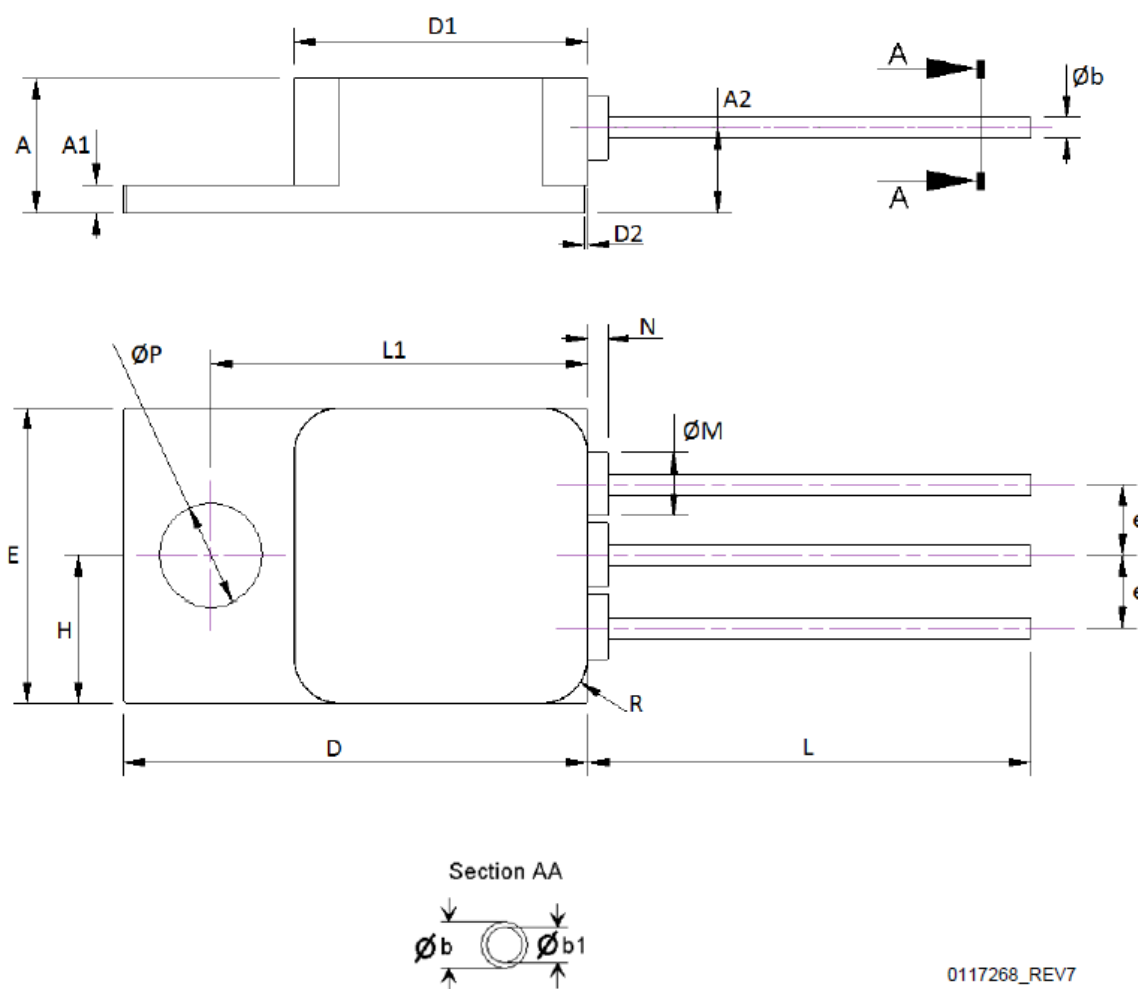
2.  $[h_{FE}]$  calculated according to method 1019 of MIL-STD-750.

## 5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 5.1 TO-257 package information

Figure 6. TO-257 package outline



0117268\_REV7

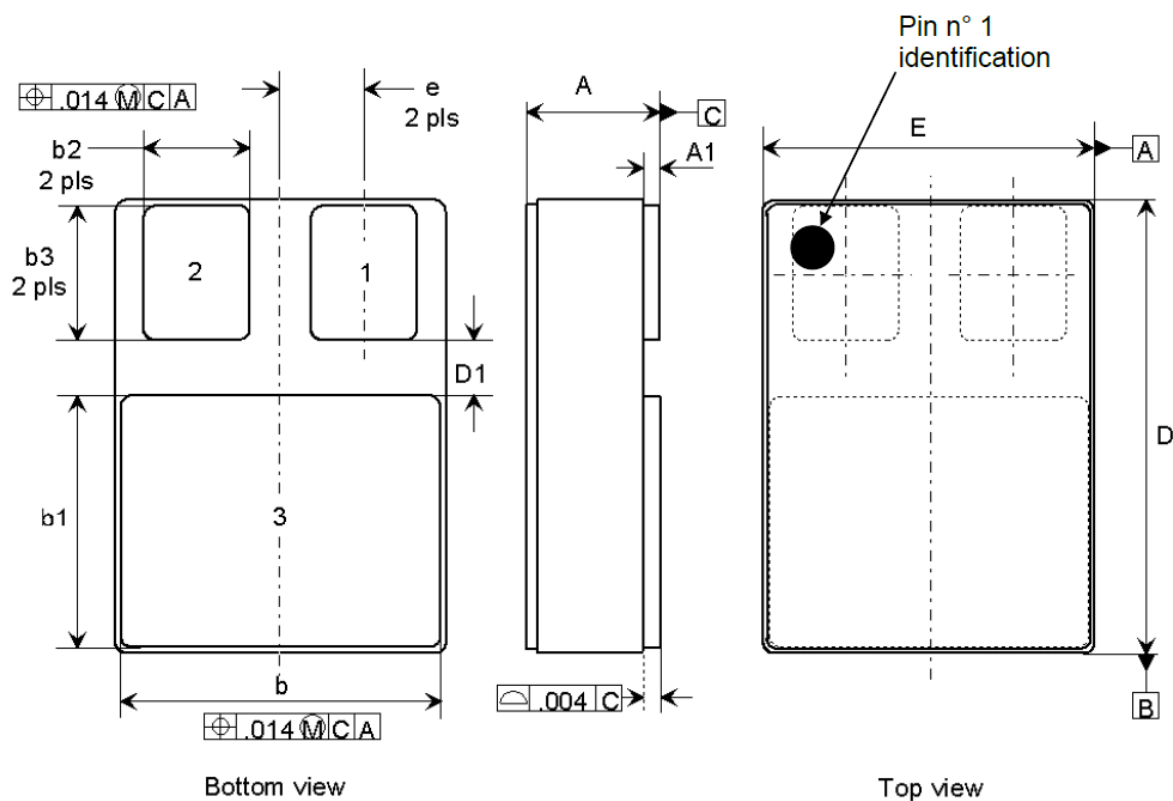
**Table 5. TO-257 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.83	4.95	5.08
A1	0.89	1.02	1.14
A2	2.91	3.05	3.18
b	0.64	-	1.02
b1	0.64	0.76	0.89
D	16.51	16.64	16.76
D1	10.41	10.54	10.67
D2	-	-	0.97
e	2.41	2.54	2.67
E	10.41	10.54	10.67
H	5.13	5.25	5.38
L	15.24	15.88	16.51
L1	13.39	13.51	13.64
M	2.16	2.29	2.41
N	-	-	0.71
P	3.56	3.68	3.81
R	-	1.65	-

*Note:* The case is not connected to any pin.

## 5.2 SMD.5 package information

Figure 7. SMD.5 package outline



7386434\_REV7

Table 6. SMD.5 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.84		3.30
A1	0.25	0.38	0.51
b	7.13	7.26	7.39
b1	5.58	5.72	5.84
b2	2.28	2.41	2.54
b3	2.92	3.05	3.18
D	10.03	10.16	10.28
D1	0.76		
E	7.39	7.52	7.64
e		1.91	

Note:

Pad 1: emitter

Pad 2: base

Pad 3: collector

- base and emitter are inverted for 2N5154RSRHRx and 2N5154SRHRx series
- the lid is not connected to any pin

## 6

## Ordering information

Table 7. Ordering information

Part number	Agency specification	Quality level	Radiation level	Pin-out	Package	Mass	Lead finish	Marking <sup>(1)</sup>	Packing
2N5154ESY1	-	Engineering model	-	-	TO-257	5 g	Gold	2N5154ESY1 + BeO	Strip pack
2N5154ESYHRG	5203/010/04	ESCC	-	-			Gold	520301004 + BeO	
2N5154ESYHRT	5203/010/05		-	-			Solder dip	520301005 + BeO	
2N5154RESYHRG	5203/010/04R		100 krad	-			Gold	520301004R + BeO	
2N5154RESYHRT	5203/010/05R		100 krad	-			Solder dip	520301005R + BeO	
2N5154S1	-	Engineering model	-	Emitter on pin 1	SMD.5	2 g	Gold	2N5154S1	Strip pack
2N5154RSHRG	5203/010/06R	ESCC	100 krad	Emitter on pin 1				520301006R	
2N5154RSHRGW	5203/010/06R	ESCC	100 krad	Emitter on pin 1				520301006R	Tape and reel
2N5154SHRG	5203/010/06	ESCC	-	Emitter on pin 1				520301006	Strip pack
2N5154SHRGW	5203/010/06	ESCC	-	Emitter on pin 1				520301006	Tape and reel
2N5154SR1	-	Engineering model	-	Emitter on pin 2				2N5154SR1	Strip pack
2N5154RSRHRG	5203/010/07R	ESCC	100 krad	Emitter on pin 2				520301007R	
2N5154RSRHRGW	5203/010/07R	ESCC	100 krad	Emitter on pin 2				520301007R	Tape and reel
2N5154SRHRG	5203/010/07	ESCC	-	Emitter on pin 2				520301007	Strip pack
2N5154SRHRGW	5203/010/07	ESCC	-	Emitter on pin 2				520301007	Tape and reel

1. Specific marking only. The full marking includes in addition: For the Engineering Models: ST logo, date code; country of origin (FR). For ESCC flight parts: ST logo, date code, country of origin (FR), ESA logo, serial number of the part within the assembly lot.

Contact ST sales office for information about specific conditions for products in die form.



## 7 Other information

### 7.1 Date code

Date code information is described in the table below.

**Table 8. Date codes**

Model	Date codes <sup>1</sup>
EM	3yywwN
ESCC	yywwN

1. yy = year, ww = week number, N = lot index in the week.

### 7.2 Documentation

Documentation is provided for each product as per below table.

**Table 9. Documentation summary**

Quality level	Radiation level	Documentation
Engineering model	-	Certificate of conformance.
ESCC	-	Certificate of conformance. ESCC qualification maintenance lot reference.
ESCC	100 Krad	Certificate of conformance. ESCC qualification maintenance lot reference. Radiation data at 30 / 50 / 70 / 100 krad at 0.1 rad / s.

## Revision history

**Table 10. Document revision history**

Date	Version	Changes
08-Jan-2009	1	Initial release.
08-Jan-2010	2	Modified Table 1: Device summary.
22-Jul-2011	3	Updated marking for the order code 2N5154ESYHRB in Table 1: Device summary.
12-Sep-2012	4	Added: Section 2.1: Electrical characteristics (curves) on page 5.
29-Jan-2014	5	Added Section 3: Radiation hardness assurance and Section 5: Ordering information. Updated Table 1: Device summary.
08-Apr-2014	6	Updated Table 1: Device summary and Table 10: Order codes. Updated Section 4: Package mechanical data. Added Figure 2.: Safe operating area. Minor text changes.
29-Jan-2016	7	Updated Figure 2.: Safe operating area. Minor text changes.
05-Apr-2016	8	Added part number 2N5154RSRHRG. Document updated accordingly. Updated Section 4: Package information.
02-May-2016	9	Updated package silhouette, Figure 1: Internal schematic diagram and Table 1: Device summary in cover page. Updated Section 4: Package information and Section 5: Ordering information. Inserted Section 6: Shipping details. Minor text changes.
28-Oct-2016	10	Added Table 6: Product mass summary.
27-Jul-2020	11	Removed TO-39 package information. Updated Section 5.1 TO-257 package information, Section 5.2 SMD.5 package information and Ordering information. Minor text changes.
25-Mar-2021	12	Updated Table 1, Figure 1 and Table 7.

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